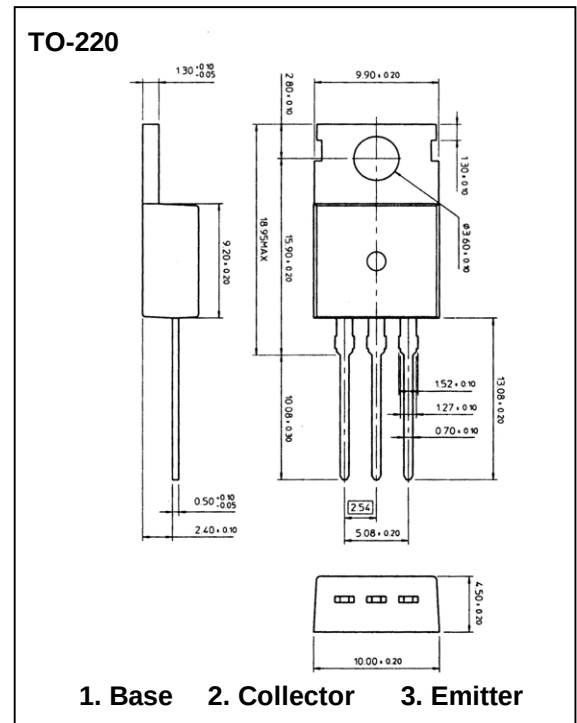


HIGH VOLTAGE SWITCHING APPLICATIONS

- Collector-Emitter Voltage: $V_{CEO}=400V$
- Collector Dissipation: $P_C(max)=1500mW$

Absolute Maximum Ratings ($T_A=25^{\circ}C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	700	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current	I_C	1500	mA
Collector Dissipation	P_C	1500	mW
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}C$



Electrical Characteristics ($T_A=25^{\circ}C$)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=1mA, I_E=0$	700		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=10mA, I_B=0$	400		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1mA, I_C=0$	9		V
Collector Cut-off Current	I_{CBO}	$V_{CB}=700V, I_E=0$		1	mA
Collector Cut-off Current	I_{CEO}	$V_{CE}=400V, I_B=0$		500	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=9V, I_C=0$		1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=0.5A$	8	40	
	$h_{FE(2)}$	$V_{CE}=10V, I_C=0.5mA$	5		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1A, I_B=250mA$		1	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1A, I_B=250mA$		1.2	V
Base-emitter Voltage	V_{BE}	$I_E=2A$		3	V
Transition Frequency	F_T	$V_{CE}=10V, I_C=100mA$ $f=1MHz$	5		MHz
Fall Time	t_f	$I_C=1A, I_{B1}=-I_{B2}=0.2mA,$		0.5	μS
Storage Time	t_s	$V_{CC}=100V$		2.5	μS

$h_{FE(1)}$ CLASSIFICATION

Classification						
$h_{FE(1)}$	8-15	15-20	20-25	25-30	30-35	35-40